

Title (en)

COMPOSITION AND CORRESPONDING METHOD FOR THE ELECTRODEPOSITION OF INDIUM COMPOSITES

Title (de)

ZUSAMMENSETZUNG UND ENTSPRECHENDES VERFAHREN ZUR GALVANISCHEN ABSCHEIDUNG VON
INDIUMVERBUNDWERKSTOFFEN

Title (fr)

COMPOSITION ET PROCÉDÉ CORRESPONDANT POUR L'ÉLECTRODEPOSITION DE COMPOSITES D'INDIUM

Publication

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Application

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Priority

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Abstract (en)

Electrochemically deposited indium composites are disclosed. The indium composites include indium metal or an alloy of indium with one or more ceramic materials. The indium composites have high bulk thermal conductivities. Articles containing the indium composites also are disclosed.

IPC 8 full level

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Citation (applicant)

- US 6653741 B2 20031125 - SREERAM ATTIGANAL N [US], et al
- US 5607570 A 19970304 - ROHBANI ELIAS [US]
- EP 0339464 A1 19891102 - NISSHIN STEEL CO LTD [JP]

Cited by

US9206519B2; CN109135685A; US2013224515A1; US9145616B2; EP1939935A3; US2013270117A1; US8491773B2; US8460533B2

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JP 2014209655 A 20141106; JP 5537004 B2 20140702; JP 5684302 B2 20150311; JP 5886903 B2 20160316; KR 101476809 B1 20141226;
KR 20090023211 A 20090304; TW 200925333 A 20090616; TW I400363 B 20130701; US 2009075102 A1 20090319;
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JP 2013026502 A 20130214; JP 2014131738 A 20140626; KR 20080084349 A 20080828; TW 97132478 A 20080826;
US 201314083188 A 20131118; US 22974608 A 20080826